

NTGS3455T1

MOSFET – P-Channel, TSOP-6

-3.5 A, -30 V

Features

- Ultra Low $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- Miniature TSOP-6 Surface Mount Package
- Pb-Free Package is Available

Applications

- Power Management in Portable and Battery-Powered Products, i.e.: Cellular and Cordless Telephones, and PCMCIA Cards

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	-30	Volts
Gate-to-Source Voltage – Continuous	V_{GS}	± 20.0	Volts
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_d	2.0	Watts
Drain Current	I_D	-3.5	Amps
– Continuous @ $T_A = 25^\circ\text{C}$	I_{DM}	-20	Amps
– Pulsed Drain Current ($T_p < 10 \mu\text{s}$)	P_d	1.0	Watts
Maximum Operating Power Dissipation	I_D	-2.5	Amps
Maximum Operating Drain Current			
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	128	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_d	1.0	Watts
Drain Current	I_D	-2.5	Amps
– Continuous @ $T_A = 25^\circ\text{C}$	I_{DM}	-14	Amps
– Pulsed Drain Current ($T_p < 10 \mu\text{s}$)	P_d	0.5	Watts
Maximum Operating Power Dissipation	I_D	-1.75	Amps
Maximum Operating Drain Current			
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Maximum Lead Temperature for Soldering Purposes for 10 Seconds	T_L	260	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

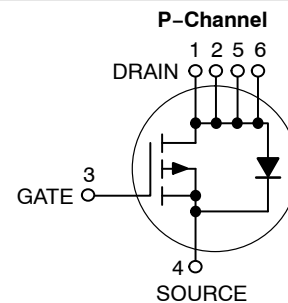
1. Mounted onto a 2" square FR-4 board (1 in sq, 2 oz. Cu. 0.06" thick single sided), $t < 5.0$ seconds.
2. Mounted onto a 2" square FR-4 board (1 in sq, 2 oz. Cu. 0.06" thick single sided), operating to steady state.



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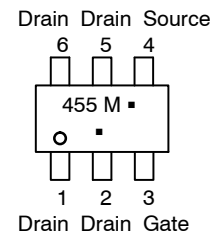
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D Max
-30 V	100 m Ω @ -10 V	-3.5 A



MARKING DIAGRAM & PIN ASSIGNMENT



**TSOP-6
CASE 318G
STYLE 1**



455 = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NTGS3455T1	TSOP-6	3000 Tape & Reel
NTGS3455T1G	TSOP-6 (Pb-Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTGS3455T1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Notes 3 & 4)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-Source Breakdown Voltage ($V_{GS} = 0 \text{ Vdc}$, $I_D = -10 \mu\text{A}$)	$V_{(BR)DSS}$	-30	-	-	Vdc
Zero Gate Voltage Drain Current ($V_{GS} = 0 \text{ Vdc}$, $V_{DS} = -30 \text{ Vdc}$, $T_J = 25^\circ\text{C}$) ($V_{GS} = 0 \text{ Vdc}$, $V_{DS} = -30 \text{ Vdc}$, $T_J = 70^\circ\text{C}$)	I_{DSS}	-	-	-1.0 -5.0	μAdc
Gate-Body Leakage Current ($V_{GS} = -20.0 \text{ Vdc}$, $V_{DS} = 0 \text{ Vdc}$)	I_{GSS}	-	-	-100	nAdc
Gate-Body Leakage Current ($V_{GS} = +20.0 \text{ Vdc}$, $V_{DS} = 0 \text{ Vdc}$)	I_{GSS}	-	-	100	nAdc

ON CHARACTERISTICS

Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = -250 \mu\text{Adc}$)	$V_{GS(th)}$	-1.0	-1.87	-3.0	Vdc
Static Drain-Source On-State Resistance ($V_{GS} = -10 \text{ Vdc}$, $I_D = -3.5 \text{ Adc}$) ($V_{GS} = -4.5 \text{ Vdc}$, $I_D = -2.7 \text{ Adc}$)	$R_{DS(on)}$	-	0.094 0.144	0.100 0.170	Ω
Forward Transconductance ($V_{DS} = -15 \text{ Vdc}$, $I_D = -3.5 \text{ Adc}$)	g_{FS}	-	6.0	-	mhos

DYNAMIC CHARACTERISTICS

Total Gate Charge	$(V_{DS} = -15 \text{ Vdc}$, $V_{GS} = -10 \text{ Vdc}$, $I_D = -3.5 \text{ Adc}$)	Q_{tot}	-	9.0	13	nC
Gate-Source Charge		Q_{gs}	-	2.5	-	
Gate-Drain Charge		Q_{gd}	-	2.0	-	
Input Capacitance	$(V_{DS} = -5.0 \text{ Vdc}$, $V_{GS} = 0 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	C_{iss}	-	480	-	pF
Output Capacitance		C_{oss}	-	220	-	
Reverse Transfer Capacitance		C_{rss}	-	60	-	

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$(V_{DD} = -20 \text{ Vdc}$, $I_D = -1.0 \text{ Adc}$, $V_{GS} = -10 \text{ Vdc}$, $R_g = 6.0 \Omega$)	$t_{d(on)}$	-	10	20	ns
Rise Time		t_r	-	15	30	
Turn-Off Delay Time		$t_{d(off)}$	-	20	35	
Fall Time		t_f	-	10	20	
Reverse Recovery Time	$(I_S = -1.7 \text{ Adc}$, $dI_S/dt = 100 \text{ A}/\mu\text{s}$)	t_{rr}	-	30	-	ns

BODY-DRAIN DIODE RATINGS

Diode Forward On-Voltage	$(I_S = -1.7 \text{ Adc}$, $V_{GS} = 0 \text{ Vdc}$)	V_{SD}	-	-0.90	-1.2	Vdc
Diode Forward On-Voltage	$(I_S = -3.5 \text{ Adc}$, $V_{GS} = 0 \text{ Vdc}$)	V_{SD}	-	-1.0	-	Vdc

3. Indicates Pulse Test: P.W. = 300 μsec max, Duty Cycle = 2%.

4. Class 1 ESD rated - Handling precautions to protect against electrostatic discharge are mandatory.

NTGS3455T1

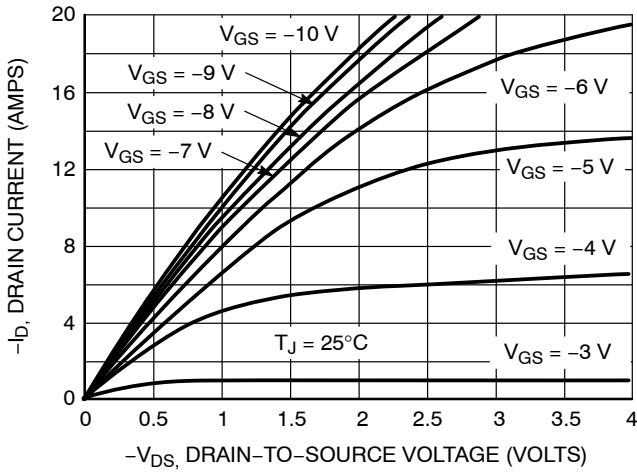


Figure 1. On-Region Characteristics

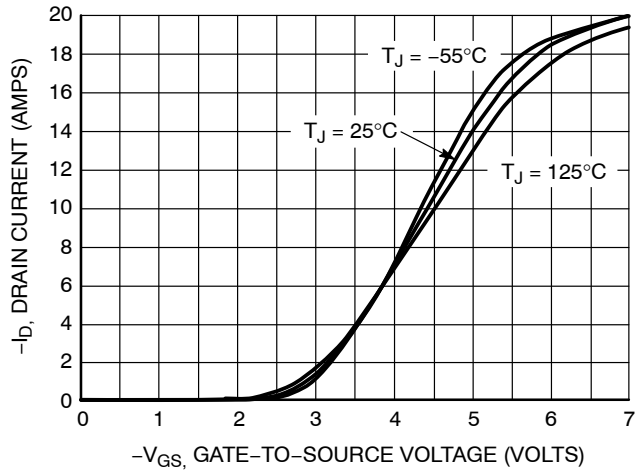


Figure 2. Transfer Characteristics

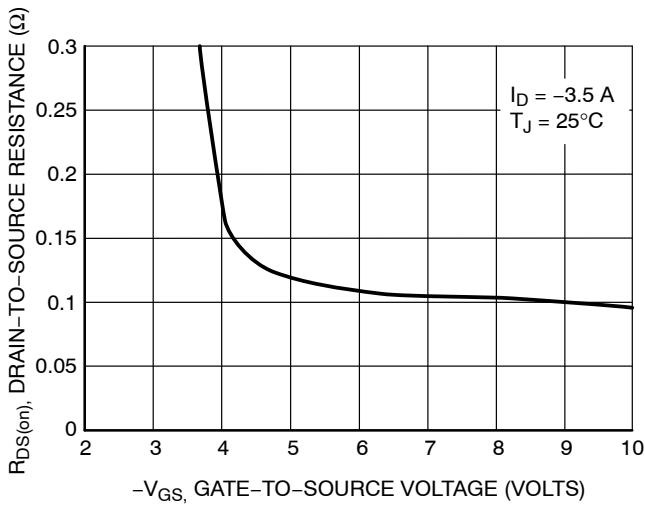


Figure 3. On-Resistance vs. Gate-to-Source Voltage

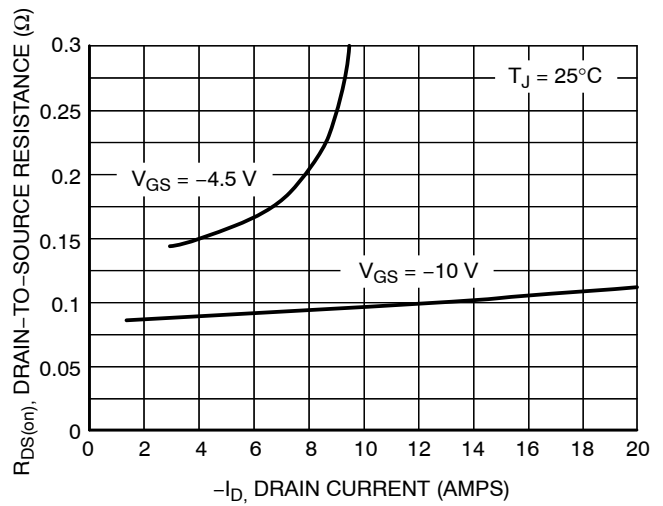


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

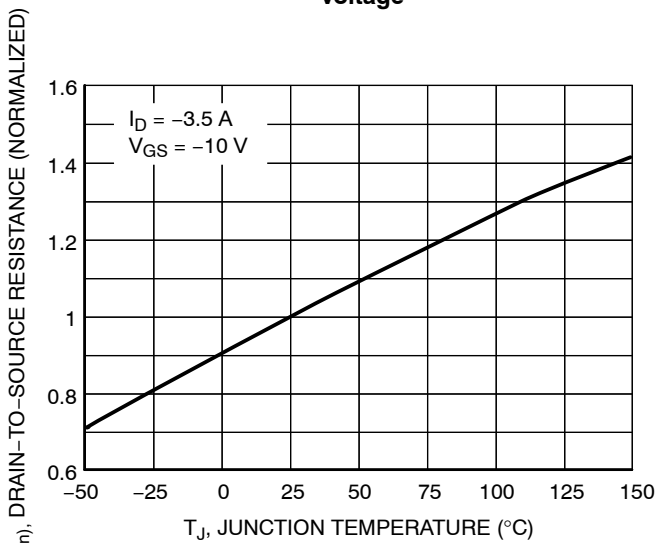


Figure 5. On-Resistance Variation with Temperature

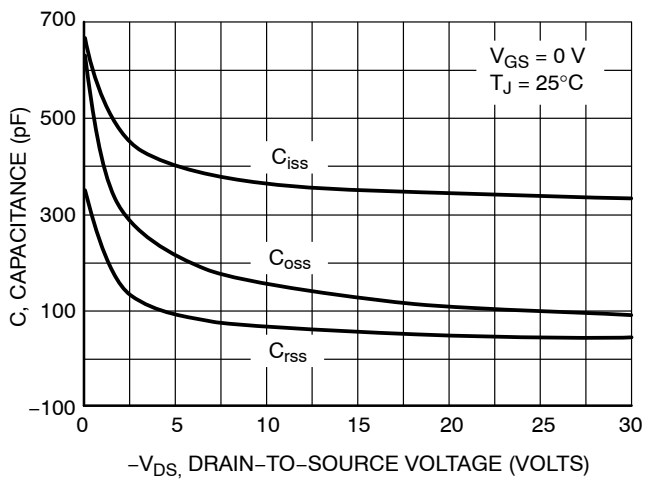


Figure 6. Capacitance Variation

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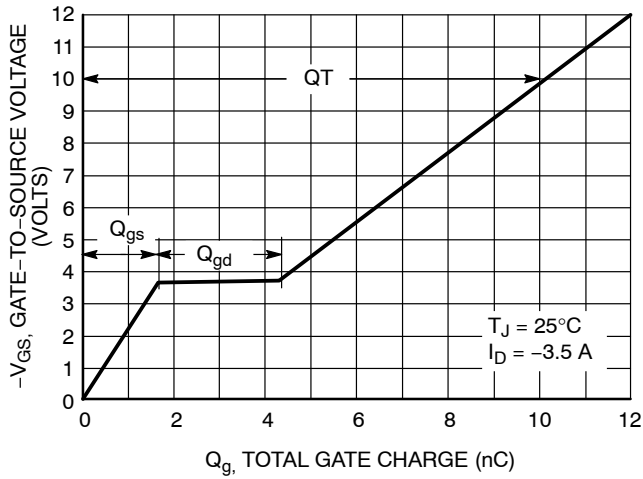


Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

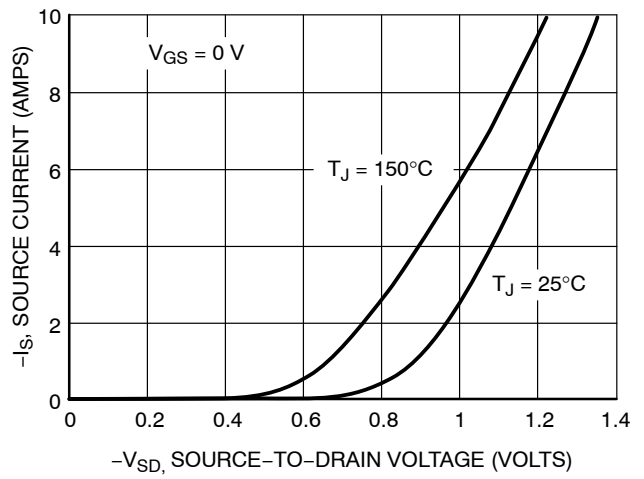


Figure 8. Diode Forward Voltage vs. Current

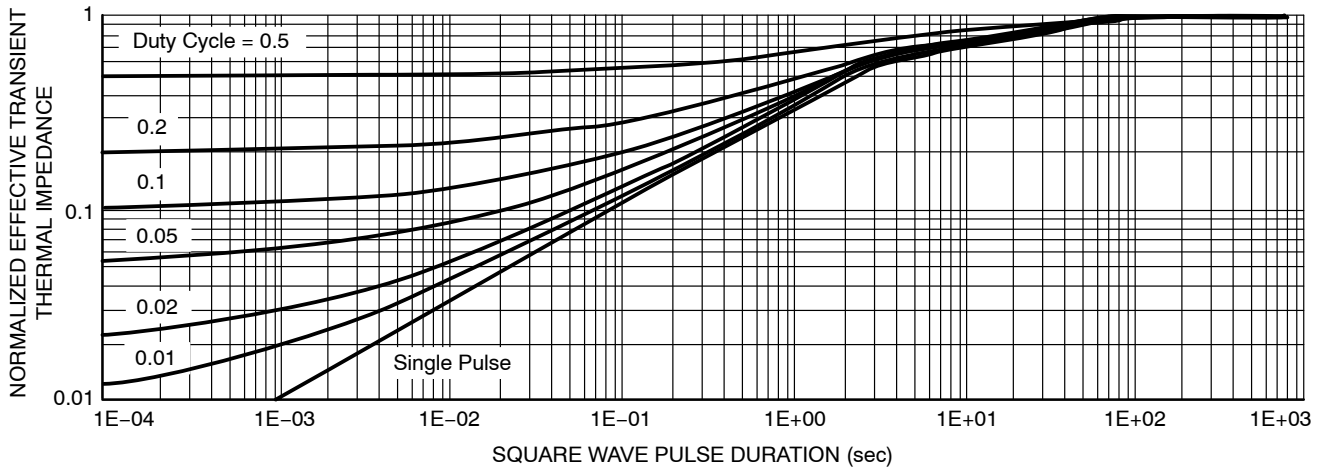


Figure 9. Normalized Thermal Transient Impedance, Junction-to-Ambient

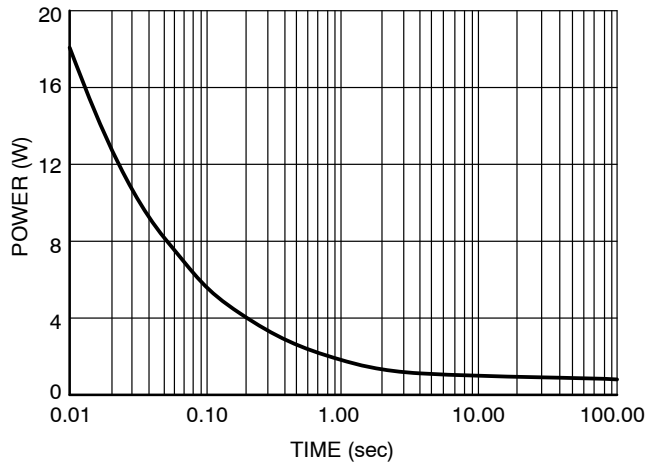


Figure 10. Single Pulse Power

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

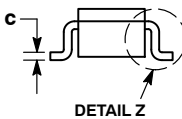
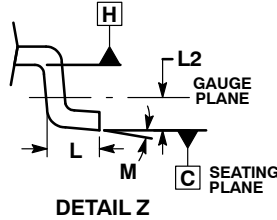
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SCALE 2:1

TSOP-6 CASE 318G-02 ISSUE V

DATE 12 JUN 2012



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
M	0°	-	10°

- | | | | | | |
|----------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------------------------------------|
| <p>STYLE 1:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN</p> | <p>STYLE 2:
PIN 1. EMITTER 2
2. BASE 1
3. COLLECTOR 1
4. EMITTER 1
5. BASE 2
6. COLLECTOR 2</p> | <p>STYLE 3:
PIN 1. ENABLE
2. N/C
3. R BOOST
4. Vz
5. V in
6. V out</p> | <p>STYLE 4:
PIN 1. N/C
2. V in
3. NOT USED
4. GROUND
5. ENABLE
6. LOAD</p> | <p>STYLE 5:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2</p> | <p>STYLE 6:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR</p> |
| <p>STYLE 7:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. N/C
5. COLLECTOR
6. EMITTER</p> | <p>STYLE 8:
PIN 1. Vbus
2. D(in)
3. D(in)+
4. D(out)+
5. D(out)
6. GND</p> | <p>STYLE 9:
PIN 1. LOW VOLTAGE GATE
2. DRAIN
3. SOURCE
4. DRAIN
5. DRAIN
6. HIGH VOLTAGE GATE</p> | <p>STYLE 10:
PIN 1. D(OUT)+
2. GND
3. D(OUT)-
4. D(IN)-
5. VBUS
6. D(IN)+</p> | <p>STYLE 11:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1/GATE 2</p> | <p>STYLE 12:
PIN 1. I/O
2. GROUND
3. I/O
4. I/O
5. VCC
6. I/O</p> |
| <p>STYLE 13:
PIN 1. GATE 1
2. SOURCE 2
3. GATE 2
4. DRAIN 2
5. SOURCE 1
6. DRAIN 1</p> | <p>STYLE 14:
PIN 1. ANODE
2. SOURCE
3. GATE
4. CATHODE/DRAIN
5. CATHODE/DRAIN
6. CATHODE/DRAIN</p> | <p>STYLE 15:
PIN 1. ANODE
2. SOURCE
3. GATE
4. DRAIN
5. N/C
6. CATHODE</p> | <p>STYLE 16:
PIN 1. ANODE/CATHODE
2. BASE
3. EMITTER
4. COLLECTOR
5. ANODE
6. CATHODE</p> | <p>STYLE 17:
PIN 1. EMITTER
2. BASE
3. ANODE/CATHODE
4. ANODE
5. CATHODE
6. COLLECTOR</p> | |

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



- | | |
|--------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------|
| <p>XXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb-Free Package</p> | <p>XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package</p> |
|--------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------|

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

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